

IN THE CLAIMS:

Please substitute the following claims for the same-numbered claims in the application:

1. (Currently Amended) A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:
a substrate;
fins extending from said substrate; and
gate dielectrics covering said fins,
wherein said gate dielectrics have different thicknesses.
2. (Currently Amended) The FinFET semiconductor structure in claim 1, wherein said fins are utilized in different types of transistors on said substrate, and wherein one type of transistor includes gate dielectrics having a first thickness and a second type of transistor includes gate dielectrics having a second thickness different than said first thickness.
3. (Currently Amended) The FinFET semiconductor structure in claim 1, wherein said fins are utilized in at least one multiple-fin transistors.
4. (Currently Amended) The FinFET semiconductor structure in claim 1, wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.
5. (Currently Amended) The FinFET semiconductor structure in claim 1, further comprising a cap over said fins.

6. (Currently Amended) The FinFET semiconductor structure in claim 5, wherein said cap comprises a different material than said gate dielectrics.
7. (Currently Amended) A semiconductor structure having at least one fin-type field effect transistor (FinFET), said semiconductor structure comprising:
 - a substrate;
 - fins extending from said substrate, wherein each of said fins comprises a central channel region and source and drain regions on opposite sides of said channel region; and
 - gate dielectrics covering said channel regions of each of said fins,wherein said gate dielectrics and said fins have different thicknesses.
8. (Currently Amended) The FinFET structure in claim 7, wherein said fins are utilized in different types of transistors on said substrate, and wherein one type of transistor includes gate dielectrics having a first thickness and a second type of transistor includes gate dielectrics having a second thickness different than said first thickness.
9. (Currently Amended) The FinFET semiconductor structure in claim 7, wherein said fins are utilized in at least one multiple-fin transistors.
10. (Currently Amended) The FinFET semiconductor structure in claim 7, wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.
11. (Currently Amended) The FinFET semiconductor structure in claim 7, further comprising a cap over said fins.
12. (Currently Amended) The FinFET semiconductor structure in claim 11, wherein said cap comprises a different material than said gate dielectrics.

13. (Currently Amended) A semiconductor structure having multiple fin-type field effect transistors (FinFETs), said semiconductor structure comprising:

a substrate;
fins extending from said substrate; and
gate dielectrics covering said fins,

wherein said fins are utilized in different types of transistors on said substrate, and wherein a first type of transistor includes gate dielectrics having a first thickness and a second type of transistor includes gate dielectrics having a second thickness different than said first thickness.

14. (Currently Amended) The FinFET semiconductor structure in claim 13, wherein said fins are utilized in multiple-fin transistors.

15. (Currently Amended) The FinFET semiconductor structure in claim 13, wherein thicker gate dielectrics comprise multiple layers of dielectric and thinner gate dielectrics comprise less layers of dielectric.

16. (Currently Amended) The FinFET semiconductor structure in claim 13, further comprising a cap over said fins.

17. (Currently Amended) The FinFET semiconductor structure in claim [[5]] 13, wherein said cap comprises a different material than said gate dielectrics.

18-34. (Canceled).